

ABSTRACT OF THE DISCLOSURE

A semiconductor device of the invention integrates a plurality of types of MOSFETs formed on its substrate in such a configuration that a gate insulator film 51 of a core-purpose MOSFET is thinner than a gate insulator film 12 of an I/O-purpose MOSFET and also a poly-silicon film 8 which is to act as a gate electrode of the core-purpose MOSFET is thinner in thickness than a poly-silicon 13 which is to act as a gate electrode of the I/O-purpose MOSFET.